

Low-Voltage Single SPDT Analog Switch

FEATURES

- Low Voltage Operation (+2.7 to +5 V)
- Low On-Resistance - $r_{DS(on)}$: 40 Ω
- Fast Switching - t_{ON} : 35 ns, t_{OFF} : 20 ns
- Low Leakage - $I_{COM(on)}$: 200-pA max
- Low Charge Injection - Q_{INJ} : 1 pC
- Low Power Consumption
- TTL/CMOS Compatible
- ESD Protection > 2000 V (Method 3015.7)
- Available in TSOP-6 and SOIC-8

BENEFITS

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space (TSOP-6)

APPLICATIONS

- Battery Operated Systems
- Portable Test Equipment
- Sample and Hold Circuits
- Cellular Phones
- Communication Systems
- Military Radio
- PBX, PABX Guidance and Control Systems

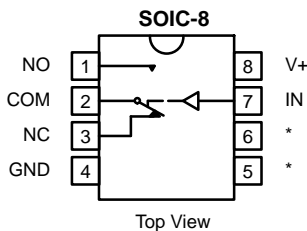
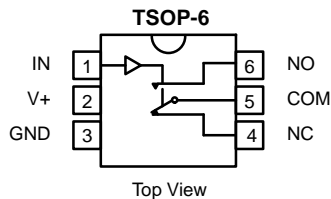
DESCRIPTION

The DG9461 is a single-pole/double-throw monolithic CMOS analog device designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 35 ns, t_{OFF} : 20 ns), low on-resistance ($r_{DS(on)}$: 40 Ω) and small physical size (TSOP-6), the DG9461 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG9461 is built on Vishay Siliconix's low voltage BCD-15 process. Minimum ESD protection, per Method 3015.7, is 2000 V. An epitaxial layer prevents latchup. Break-before-make is guaranteed for DG9461.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



*Not Connected

| TRUTH TABLE | | |
|-------------|-----|-----|
| Logic | NC | NO |
| 0 | ON | OFF |
| 1 | OFF | ON |

Logic "0" ≤ 0.8 V
Logic "1" ≥ 2.4 V

| ORDERING INFORMATION | | |
|----------------------|---------|-------------|
| Temp Range | Package | Part Number |
| -40 to 85°C | TSOP-6 | DG9461DV |
| | SOIC-8 | DG9461DY |



ABSOLUTE MAXIMUM RATINGS

Reference to GND

V+ -0.3 to +13 V

IN, COM, NC, NO^a -0.3 to (V+ + 0.3 V)

Continuous Current (Any terminal) ± 20 mA

Peak Current ± 40 mA

(Pulsed at 1ms, 10% duty cycle)

ESD (Method 3015.7) > 2000 V

Storage Temperature (D Suffix) -65 to 125°C

Power Dissipation (Packages)^b8-Pin Narrow Body SOIC^c 400 mW

Notes:

a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC Board.

c. Derate 6.5 mW/°C above 75°C

| SPECIFICATIONS (V+ = 3 V) | | | | | | | |
|---|---------------------|---|-------------------|-------------------------|------------------|------------------|------|
| Parameter | Symbol | Test Conditions Otherwise Unless Specified V+ = 3 V, ± 10%, VIN = 0.8 or 2.4 V ^e | Temp ^a | D Suffix −40 to 85°C | | | Unit |
| | | | | Min ^c | Typ ^b | Max ^c | |
| Analog Switch | | | | | | | |
| Analog Signal Range ^d | VANALOG | | Full | 0 | | 3 | V |
| Drain-Source On-Resistance | rDS(on) | VNO or VNC = 1.5 V, V+ = 2.7 V ICOM = 5 mA | Room Full | | 50 | 80 140 | Ω |
| rDS(on) Match ^d | ΔrDS(on) | VNO or VNC = 1.5 V | Room | | 0.4 | 2 | |
| rDS(on) Flatness ^f | rDS(on) Flatness | VNO or VNC = 1 and 2 V | Room | | 4 | 8 | |
| NO or NC Off Leakage Current ^g | INO/NC(off) | VNO or VNC = 1 V / 2 V, VCOM = 2 V / 1 V | Room Full | −100 −5000 | 5 | 100 5000 | pA |
| COM Off Leakage Current ^g | ICOM(off) | VCOM = 1 V / 2 V, VNO or VNC = 2 V / 1 V | Room Full | −100 −5000 | 5 | 100 5000 | |
| Channel-On Leakage Current ^g | ICOM(on) | VCOM = VNO or VNC = 1 V / 2 V | Room Full | −200 −10000 | 10 | 200 10000 | |
| Digital Control | | | | | | | |
| Input Current | IINL or IINH | | Full | | 1 | | μA |
| Dynamic Characteristics | | | | | | | |
| Turn-On Time | tON | VNO or VNC = 1.5 V | Room Full | | 50 | 120 200 | ns |
| Turn-Off Time | tOFF | | Room Full | | 20 | 50 120 | |
| Break-Before-Make Time | td | | Room | 3 | 20 | | |
| Charge Injection | QINJ | CL = 1 nF, Vgen = 0 V, Rgen = 0 Ω | Room | | 1 | 5 | pC |
| Off-Isolation | OIRR | RL = 50 Ω, CL = 5 pF, f = 1 MHz | Room | | −74 | | dB |
| Source-Off Capacitance | CS(off) | f = 1 MHz | Room | | 7 | | pF |
| Channel-On Capacitance | CD(on) | | Room | | 32 | | |
| Power Supply | | | | | | | |
| Power Supply Range | V+ | | | 2.7 | | 12 | V |
| Power Supply Current | I+ | V+ = 3.3 V, VIN = 0 or 3.3 V | | | | 1 | μA |

Notes:

a. Room = 25°C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.

f. Difference of min and max values.

g. Guraranteed by 5-V leakage testing, not production tested..

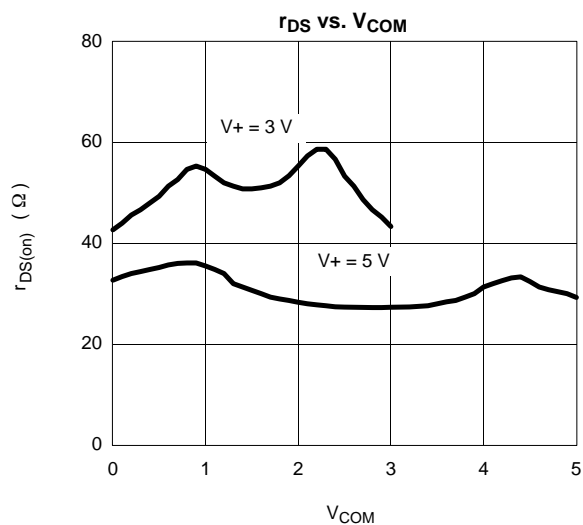
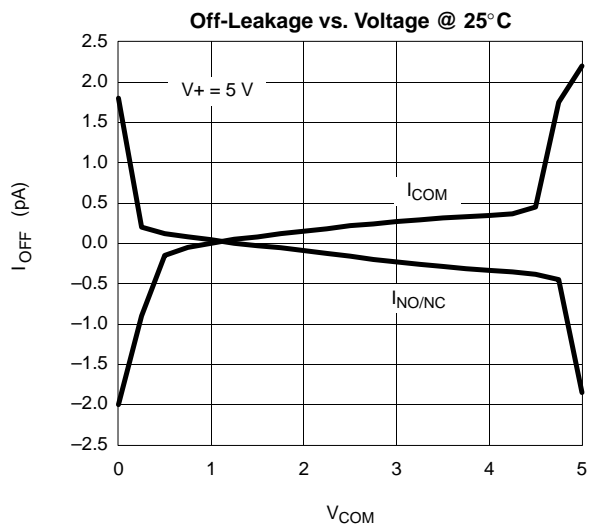
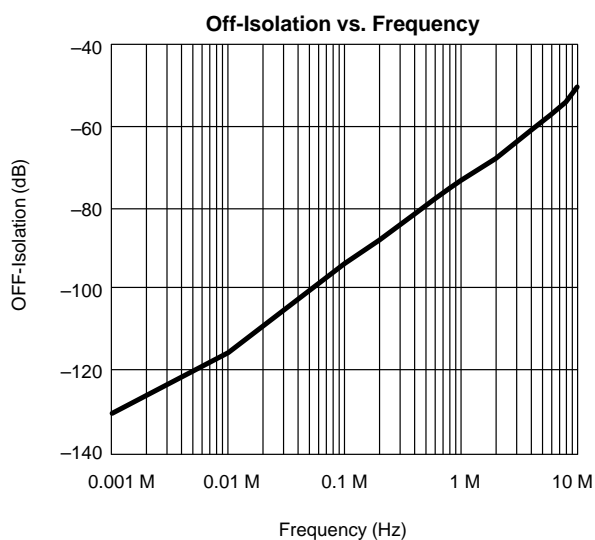
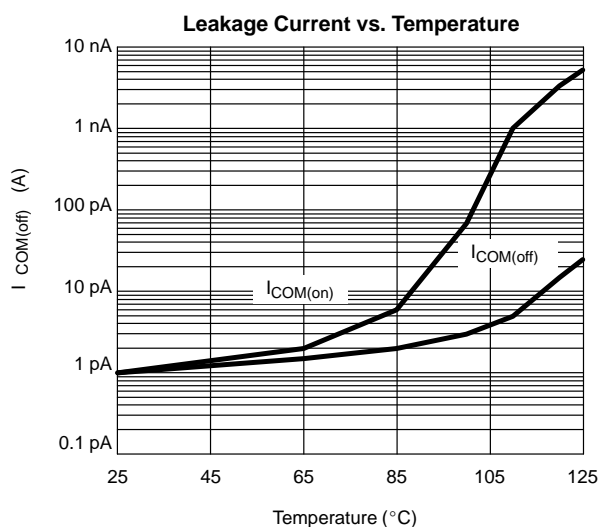
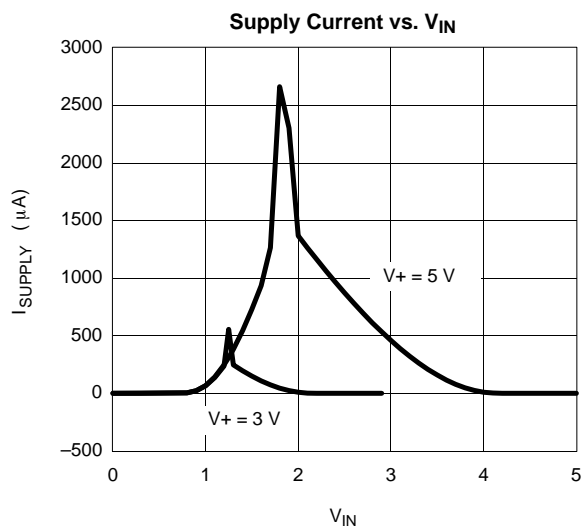
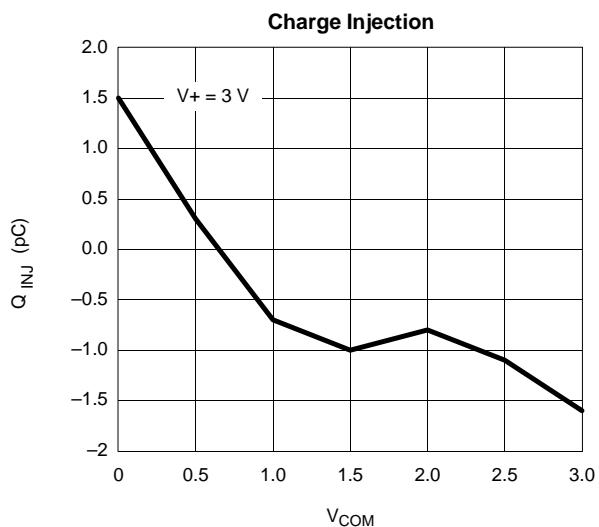


| SPECIFICATIONS (V+ = 5 V) | | | | | | | |
|---|--------------------------------------|--|-------------------|-------------------------|------------------|------------------|------|
| Parameter | Symbol | Test Conditions Otherwise Unless Specified V+ = 5 V, ±10%, VIN = 0.8 or 2.4 V ^e | Temp ^a | D Suffix –40 to 85°C | | | Unit |
| | | | | Min ^c | Typ ^b | Max ^c | |
| Analog Switch | | | | | | | |
| Analog Signal Range ^d | V _{ANALOG} | | Full | 0 | | 5 | V |
| Drain-Source On-Resistance | r _{DS(on)} | V _{NO} or V _{NC} = 3.5 V, V+ = 4.5 V I _{COM} = 5 mA | Room Full | | 30 | 60 75 | Ω |
| r _{DS(on)} Match ^d | Δr _{DS(on)} | V _{NO} or V _{NC} = 1.5 V | Room | | 0.4 | 2 | |
| r _{DS(on)} Flatness ^f | r _{DS(on)} Flatness | V _{NO} or V _{NC} = 1, 2, and 3 V | Room | | 2 | 6 | |
| NO or NC Off Leakage Current | I _{NO/NC(off)} | V _{NO} or V _{NC} = 1 V / 4 V, V _{COM} = 4 V / 1 V | Room Full | –100 –5000 | 10 | 100 5000 | pA |
| COM Off Leakage Current | I _{COM(off)} | V _{COM} = 1 V / 4 V, V _{NO} or V _{NC} = 4 V / 1 V | Room Full | –100 –5000 | 10 | 100 5000 | |
| Channel-On Leakage Current | I _{COM(on)} | V _{COM} = V _{NO} or V _{NC} = 1 V / 4 V | Room Full | –200 –10000 | | 200 10000 | |
| Digital Control | | | | | | | |
| Input Current | I _{INL} or I _{INH} | | Full | | 1 | | μA |
| Dynamic Characteristics | | | | | | | |
| Turn-On Time | t _{ON} | V _{NO} or V _{NC} = 3.0 V | Room Full | | 35 | 75 150 | ns |
| Turn-Off Time | t _{OFF} | | Room Full | | 20 | 50 100 | |
| Break-Before-Make Time | t _d | | Room | 3 | 10 | | |
| Charge Injection | Q _{INJ} | C _L = 1 nF, V _{gen} = 0 V, R _{gen} = 0 Ω | Room | | 2 | 5 | pC |
| Off-Isolation | OIRR | R _L = 50 Ω, C _L = 5 pF, f = 1 MHz | Room | | –74 | | dB |
| NC and NO Capacitance | C _(off) | f = 1 MHz | Room | | –7 | | pF |
| Channel-On Capacitance | C _{D(on)} | | Room | | 32 | | |
| Power Supply | | | | | | | |
| Power Supply Range | V+ | | | 2.7 | | 12 | V |
| Power Supply Current | I+ | V+ = 5.5 V, VIN = 0 or 5.5 V | | | | 1 | μA |

Notes:

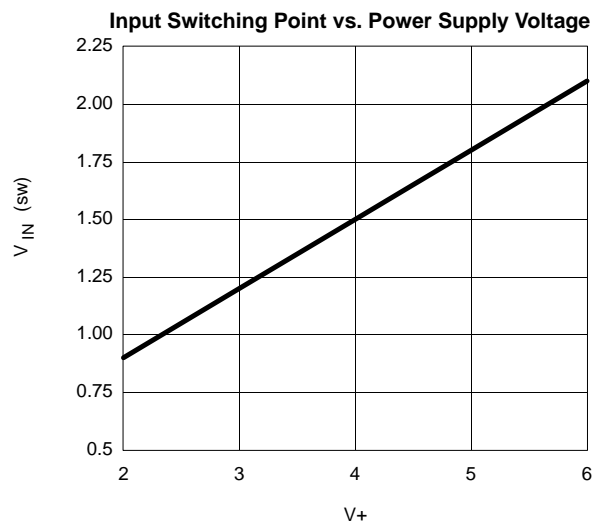
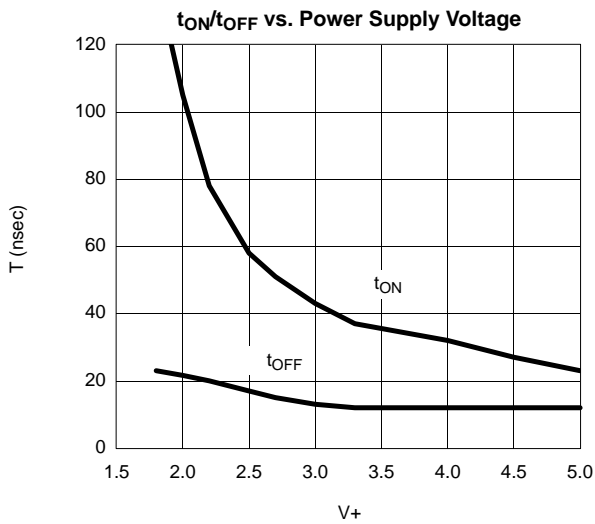
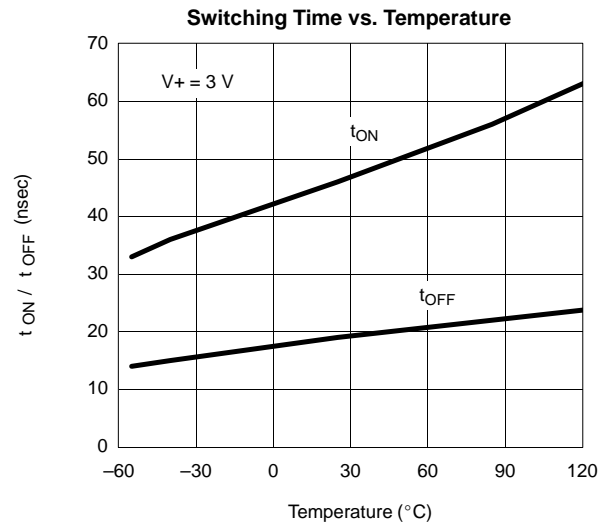
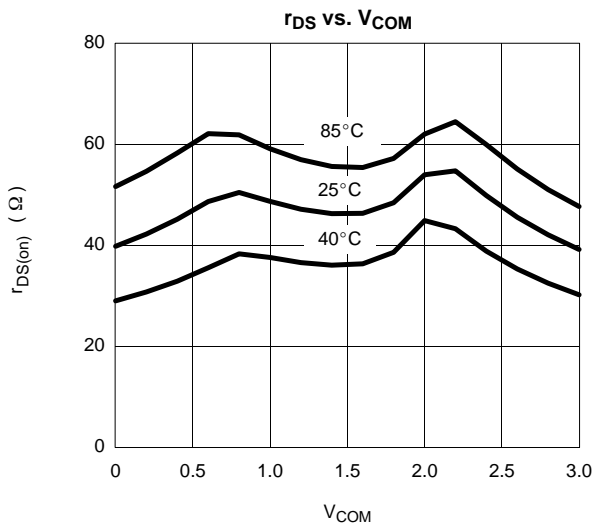
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- V_{IN} = input voltage to perform proper function.
- Difference of min and max values.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

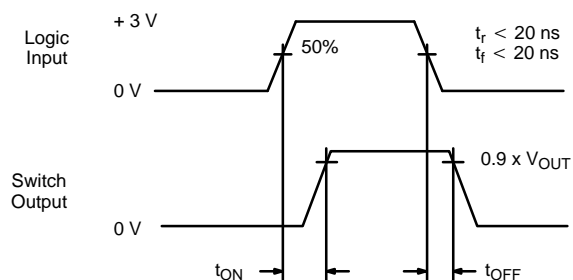
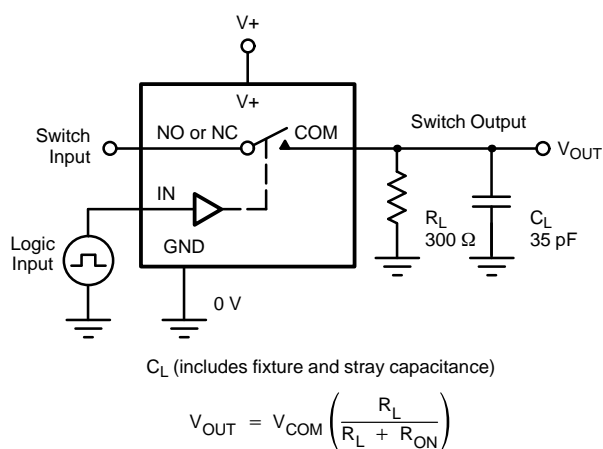




TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TEST CIRCUITS



Logic "1" = Switch On
Logic input waveforms inverted for switches that have the opposite logic sense.

FIGURE 1. Switching Time

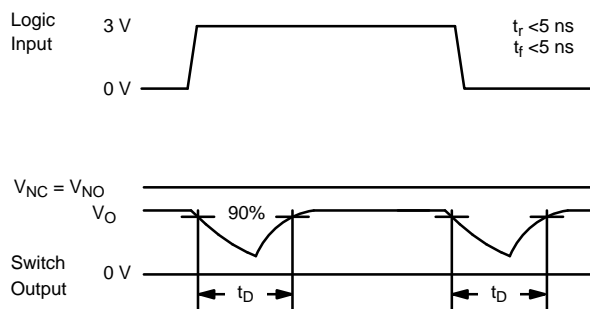
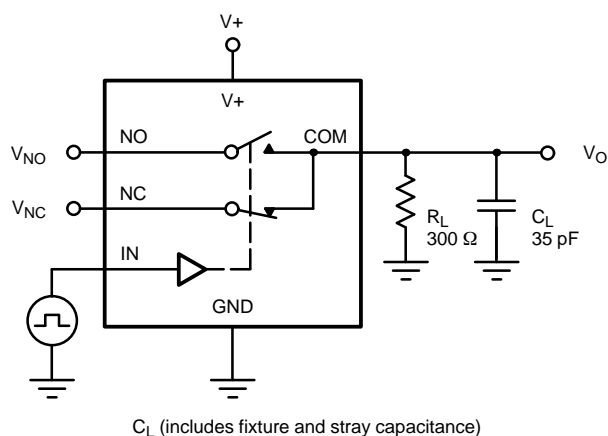
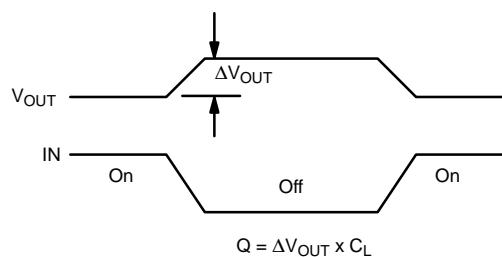
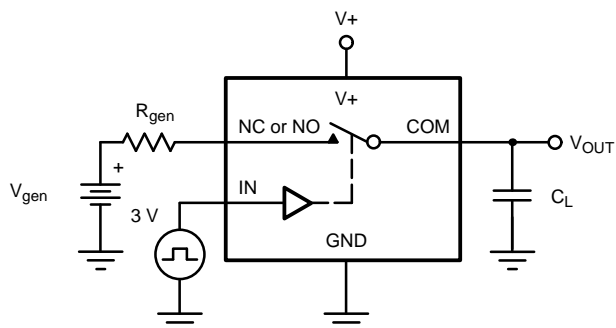


FIGURE 2. Break-Before-Make Interval



IN depends on switch configuration: input polarity determined by sense of switch.

FIGURE 3. Charge Injection

TEST CIRCUITS

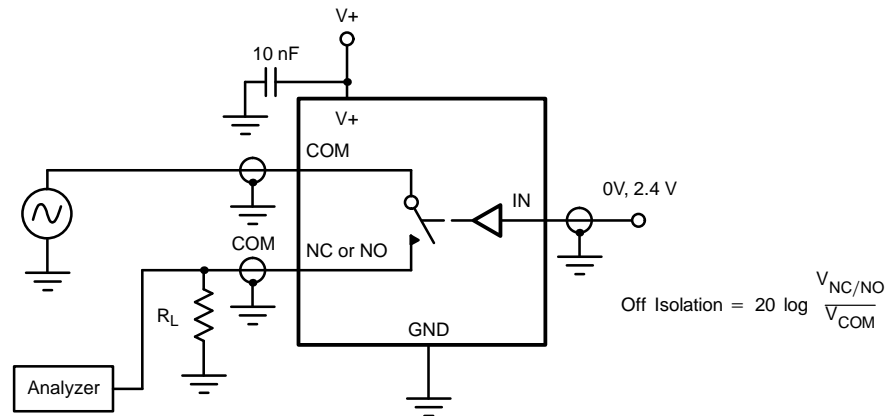


FIGURE 4. Off-Isolation

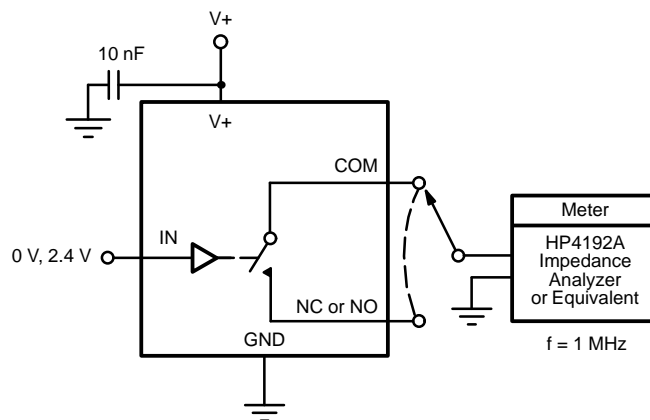


FIGURE 5. Channel Off/On Capacitance